



**晶体管**  
**TRANSISTOR**  
**C945AF**

**主要参数 MAIN CHARACTERISTICS**

I <sub>c</sub>	150mA
V <sub>CEO</sub>	52V
V <sub>CB0</sub>	70V
P <sub>c</sub>	400mW

**产品特性 FEATURES**

硅外延	Epitaxial silicon
高开关速度	High switching speed
RoHS 产品	RoHS product

**用途 APPLICATIONS**

高频开关电源	High frequency switch power supply
一般功率放大电路	Commonly power amplifier circuit
高频功率变换	High frequency power transform

**封装形式 Package**



**绝对最大额定值 ABSOLUTE RATINGS (T<sub>c</sub>=25°C)**

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
集电极—基极直流电压 Collector- Base Voltage ( I <sub>E</sub> =0)	V <sub>CB0</sub>	70	V
集电极—发射极直流电压 Collector- Emitter Voltage ( I <sub>B</sub> =0)	V <sub>CEO</sub>	52	V
发射极—基极直流电压 Emitter-Base Voltage ( I <sub>C</sub> =0)	V <sub>EBO</sub>	5.5	V
最大集电极直流电流 Collector Current ( DC)	I <sub>c</sub>	150	mA
最大集电极耗散功率 Total Dissipation (TO-92)	P <sub>c</sub>	400	mW
最高结温 Junction Temperature	T <sub>j</sub>	150	°C
贮存温度 Storage Temperature	T <sub>stg</sub>	-55~+150	°C

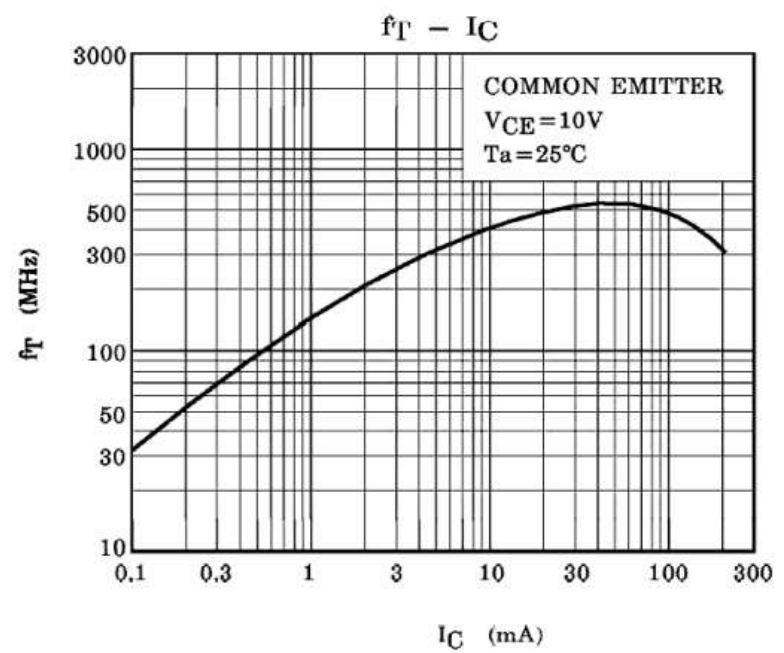
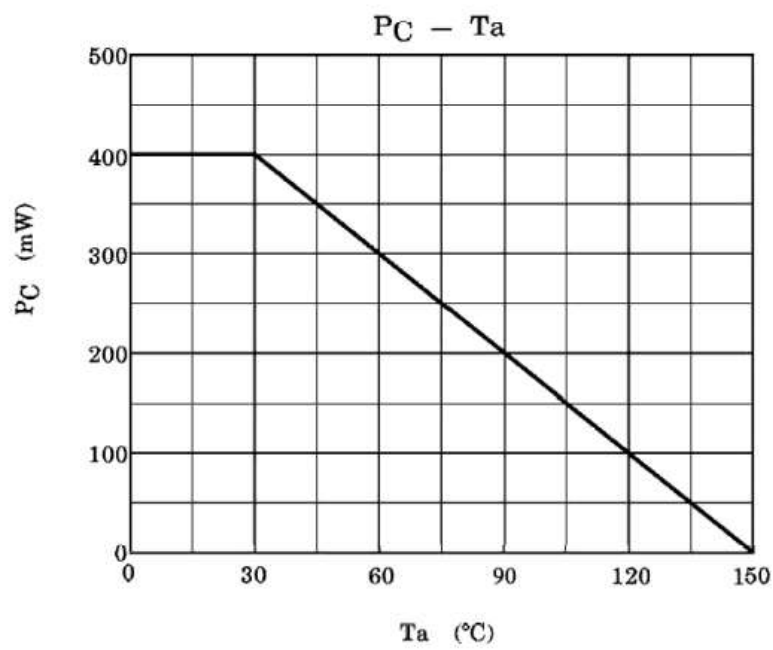
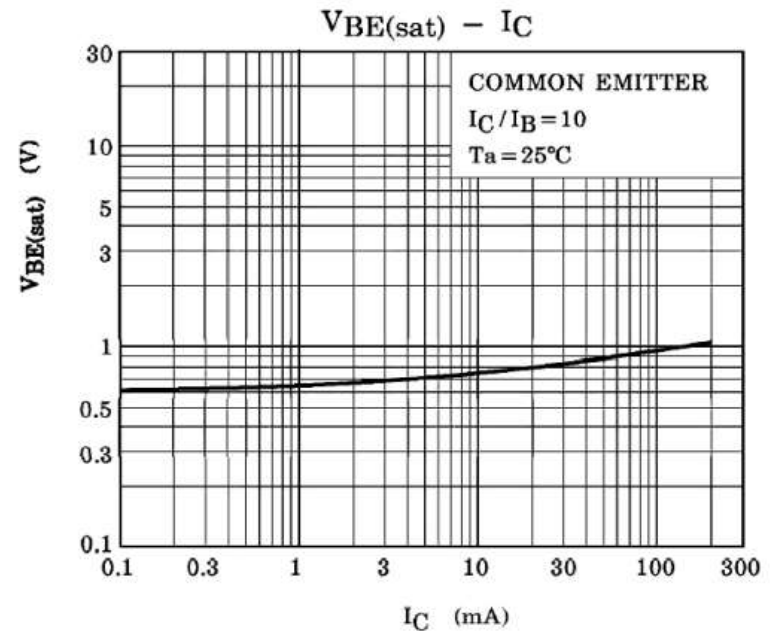
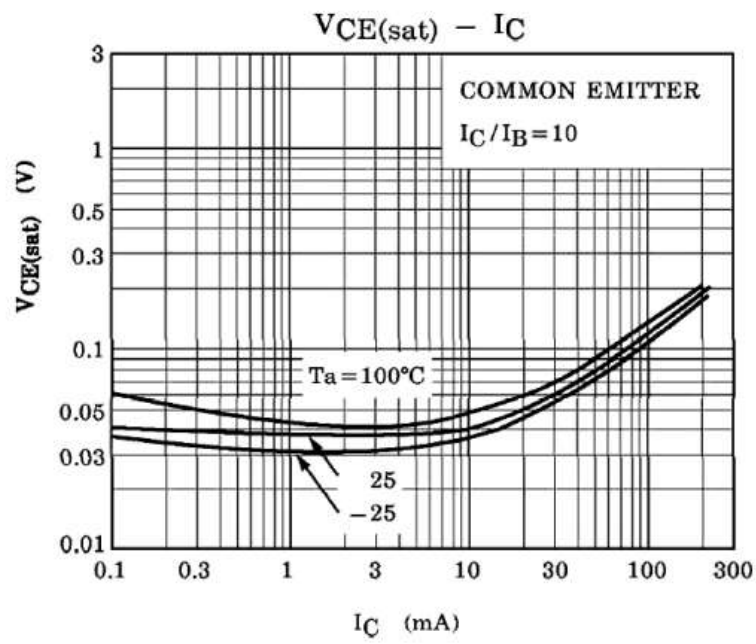
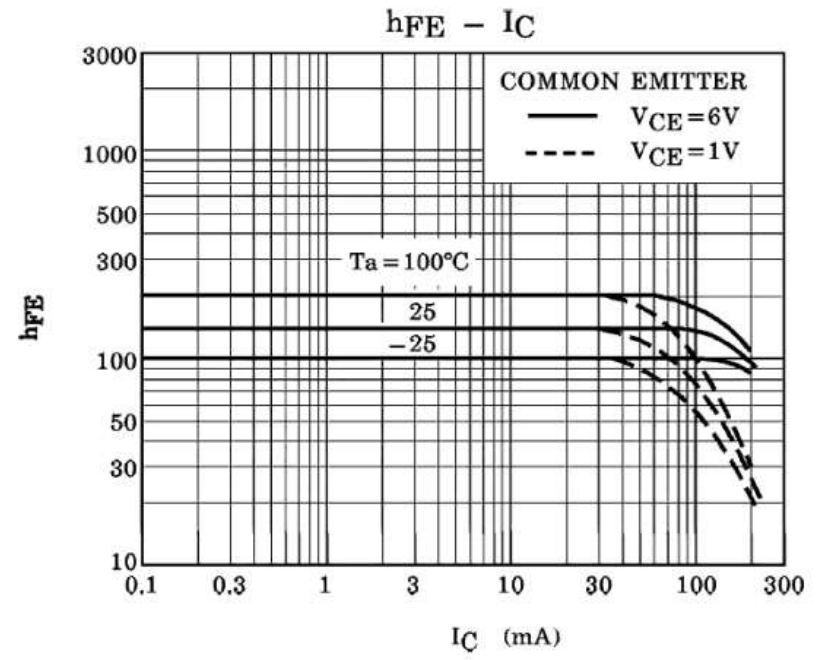
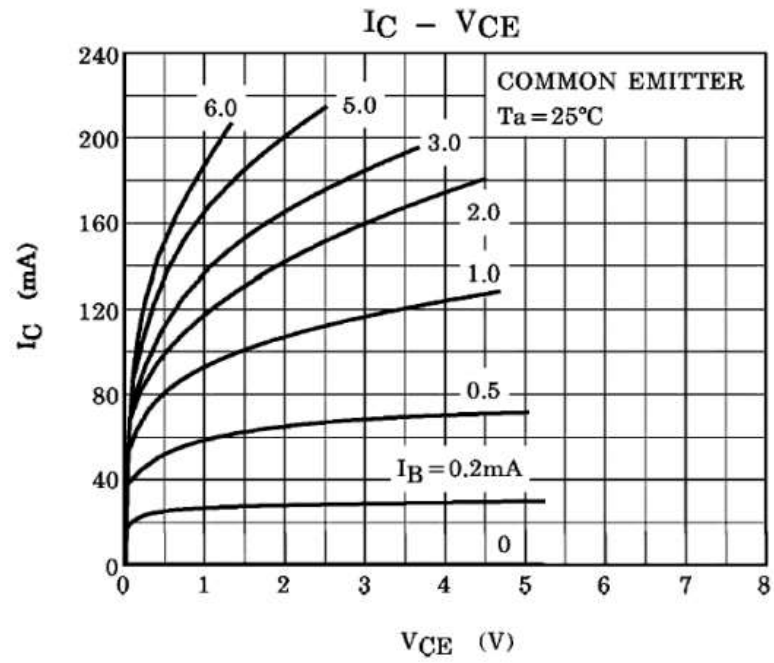
## 电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	测试条件 Tests conditions	最小值 (min)	典型值 (typ)	最大值 (max)	单位 Unit
$V(BR)_{CBO}$	$I_C=100\mu A, I_E=0$	70	-	-	V
$V(BR)_{CEO}$	$I_C=2mA, I_B=0$	52	-	-	V
$V(BR)_{EBO}$	$I_E=100\mu A, I_C=0$	5.5	-	-	V
$I_{CBO}$	$V_{CB}=50V, I_E=0$	-	-	100	nA
$I_{EBO}$	$V_{EB}=5V, I_C=0$	-	-	100	nA
$H_{fe}(1)$	$V_{CE}=6V, I_C=2mA$	90	-	600	-
$H_{fe}(2)$	$V_{CE}=6V, I_C=150mA$	25	-	-	-
$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$	-	-	0.3	V
$V_{BE(sat)}$	$I_C=100mA, I_B=10mA$	-	-	1.1	V

### 放大倍数 $h_{FE}$ Classifications

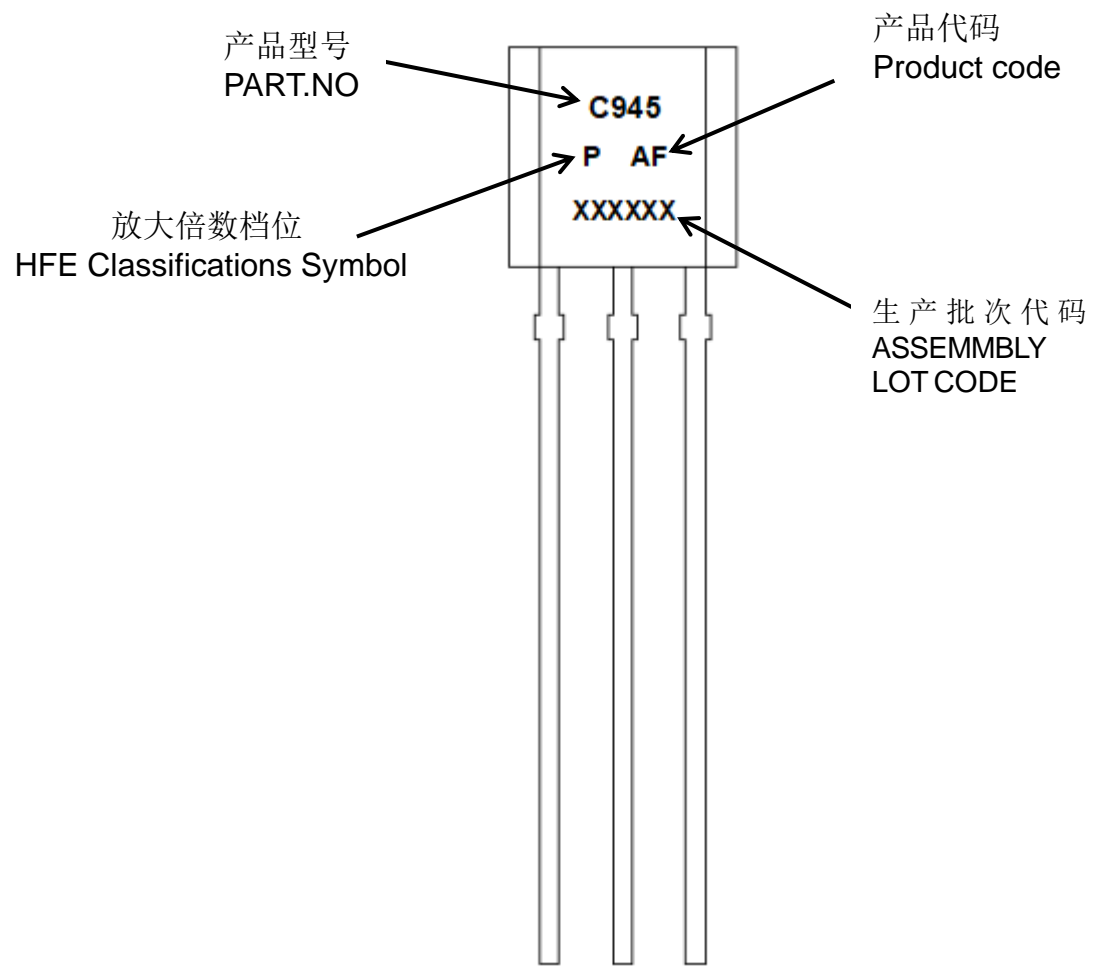
$h_{FE}$ Classifications Symbol	R	Q	P	K
$h_{FE}$ Range	90-180	135-270	200-400	300-600

# 典型特性曲线 Electrical Characteristics



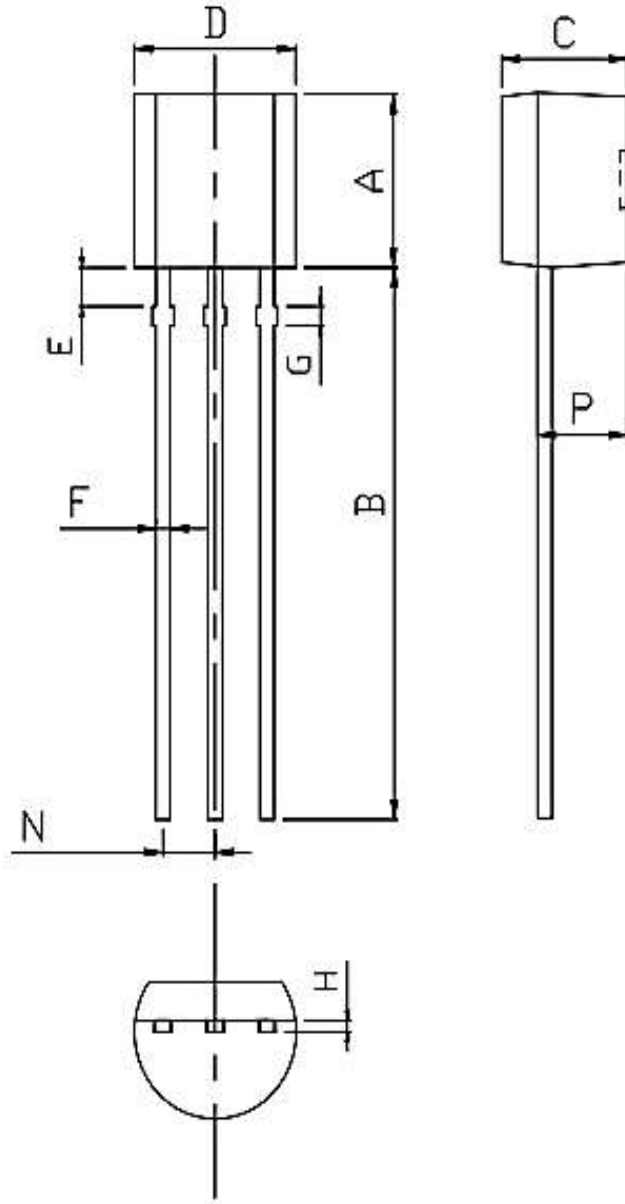
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**印记 Marking:**



外形尺寸：  
Package Dimension

T0-92



DIM	MILLIMETERS
A	4.55+0.20
B	14.50±0.30
C	3.54±0.20
D	4.56±0.20
E	1.30±0.20
F	0.46±0.20
G	0.50±0.10
H	0.32±0.10
N	1.30±0.20
P	2.52±0.20

Unit : (mm)